

Appl. No. 10/604,895
Amdt. dated October 20, 2004
Reply to Office action of August 09, 2004

REMARKS/ARGUMENTS

1. Rejection of claims 1-3,5-9, 11-13, and 15-16 under 35 U.S.C. 103(a) as being unpatentable over Hsu (US 6,207,556) in view of Iriki (US 20020081758) and Wolf and Tauber (pp. 429-434, 518-520):

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Claims 1 and 11 are amended to overcome this rejection. Specifically, the limitation of "the first dielectric layer and the second dielectric layer being composed of spin-on glass (SOG) materials" is added. These amendments are fully supported in the specification, for instance in
10 paragraphs [0014] and [0016]. No new matter is entered.

With regard to US 6,207,556, Hsu discloses a method of fabricating a metal interconnect. Hsu's teaching includes forming a plurality of metal lines 202 on a semiconductor substrate 200, and forming a conformal
15 silicon-rich oxide dielectric layer 204 over the metal lines 202 by a CVD process.

Pertaining to US 20020081758, Iriki discloses a method of manufacturing a semiconductor integrated circuit device that includes
20 depositing a first resist film for patterning a wafer, evaluating the developed pattern, removing the first resist film if it fails the evaluation, and re-applying a second resist film on the wafer.

Wolf and Tauber teach that resist can be removed by wet etching or
25 by dry etching processes. Wolf and Tauber also teach that a wafer needs to

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be cleaned and free of moisture prior to applying resist, and that the wafer can be cleaned by brush scrubbing and dehydrated by baking.

- 5 In Iriki's teaching, the resist film (photoresist film) is used to define the patterns of at least a thin film formed prior to the resist film, and the resist film is then removed after the patterns are defined by photolithography processes. On the contrary, the dielectric film which passes the examining step is retained on the semiconductor wafer. In
10 addition, the applicant notes that claims 4 and 14 which recite the limitation "the first dielectric layer and the second dielectric layer being composed of spin-on glass (SOG) materials" would be allowable because the prior art of record does not teach or suggest this in combination with other limitations included in claims 1 and 11 as the examiner has stated.
15 Thus, the applicant contends that the amended claims 1 and 11 including "the first dielectric layer and the second dielectric layer being composed of spin-on glass (SOG) materials" should be patentable over Hsu in view of Iriki and Wolf and Tauber. Claims 2-3, 5-9 and 12-13, 15-16 are respectively dependent on claims 1 and 11 and should be allowed if claims
20 1 and 11 are allowed.

Reconsideration of claims 1-3, 5-9, 11-13, and 15-16 is politely requested.

- 25 **2. Objection to claims 4, 10, 14, 17 as being dependant upon a rejected base claim:**

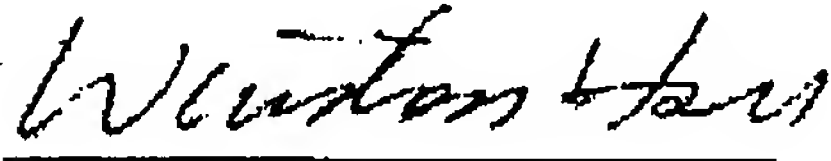
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Claims 4, 10, 14, 17 would be allowable if rewritten in independent form to include all limitations of the base claim and any intervening claim for reasons of record. The applicant notes this allowance, and believes the
5 limitations included in claims 4 and 14 suffice for differentiating from the cited prior arts. Thus, reconsideration of claims 10 and 17 is politely requested in view of the amendments made to claims 1 and 11.

Applicant respectfully requests that a timely Notice of Allowance be
10 issued in this case.

Sincerely yours,

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